



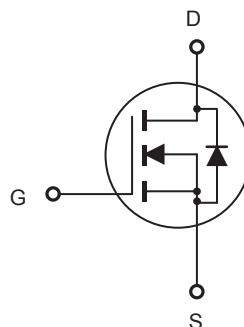
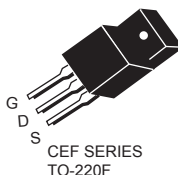
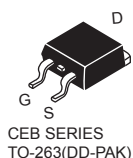
CEPF630/CEBF630 ☐ CEFF630

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEPF630	200V	0.35Ω	10A	10V
CEBF630	200V	0.35Ω	10A	10V
CEFF630	200V	0.35Ω	10A ^d	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead free product is acquired.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V _{DS}	200		V
Gate-Source Voltage	V _{GS}	±20		V
Drain Current-Continuous	I _D	10	10 ^d	A
Drain Current-Pulsed ^a	I _{DM} ^e	40	40 ^d	A
Maximum Power Dissipation @ T _C = 25°C - Derate above 25°C	P _D	75	33	W
		0.6	0.27	W/°C
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 150		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	1.5	3.7	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W



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Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

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Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	200			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 160V, V_{GS} = 0V$			25	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
On Characteristics ^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	2		4	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5A$			350	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 5A$		6		S
Dynamic Characteristics ^c						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		680		pF
Output Capacitance	C_{oss}			105		pF
Reverse Transfer Capacitance	C_{rss}			40		pF
Switching Characteristics ^c						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100V, I_D = 5A,$ $V_{GS} = 10V, R_{GEN} = 50\Omega$		50	100	ns
Turn-On Rise Time	t_r			80	160	ns
Turn-Off Delay Time	$t_{d(off)}$			55	110	ns
Turn-Off Fall Time	t_f			40	80	ns
Total Gate Charge	Q_g	$V_{DS} = 160V, I_D = 5.9A,$ $V_{GS} = 10V$		27	54	nC
Gate-Source Charge	Q_{gs}			4		nC
Gate-Drain Charge	Q_{gd}			14.7		nC
Drain-Source Diode Characteristics and Maximun Ratings						
Drain-Source Diode Forward Current	I_S				10	A
Drain-Source Diode Forward Voltage ^b	V_{SD}	$V_{GS} = 0V, I_S = 10A$			1.5	V
Notes : ^a Repetitive Rating : Pulse width limited by maximum junction temperature . ^b Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. ^c Guaranteed by design, not subject to production testing. ^d Limited only by maximum temperature allowed . ^e Pulse width limited by safe operating area . ^f Full package $I_{S(max)} = 6.4A$. ^g Full package V_{SD} test condition $I_S = 6.4A$.						



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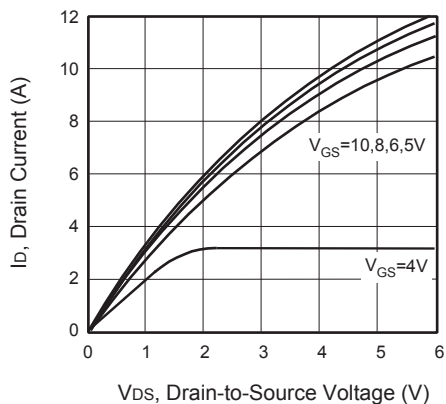


Figure 1. Output Characteristics

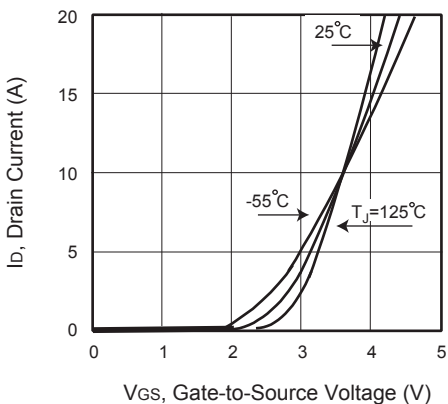


Figure 2. Transfer Characteristics

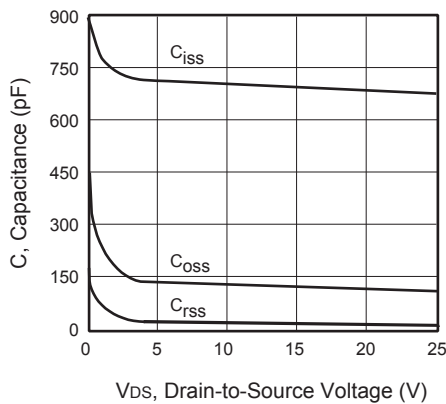


Figure 3. Capacitance

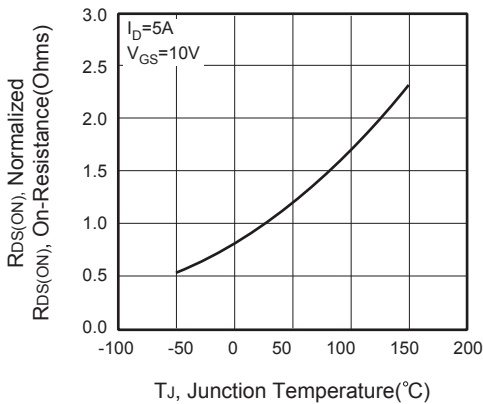


Figure 4. On-Resistance Variation with Temperature

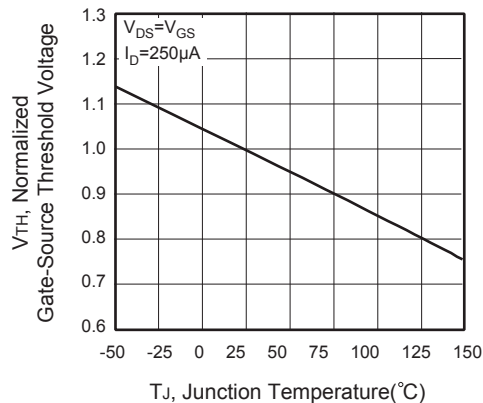


Figure 5. Gate Threshold Variation with Temperature

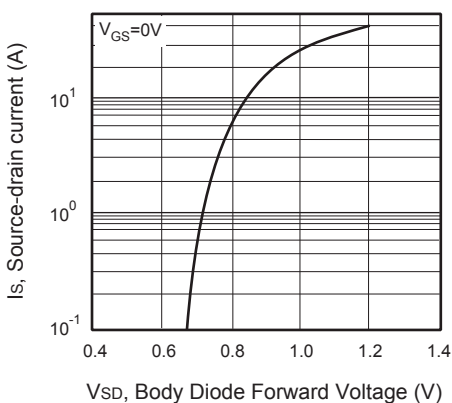


Figure 6. Body Diode Forward Voltage Variation with Source Current



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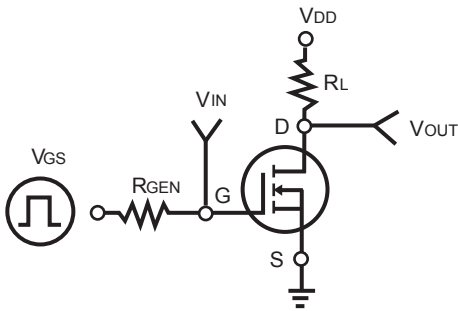
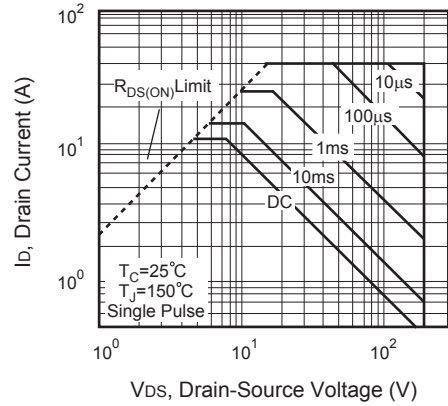
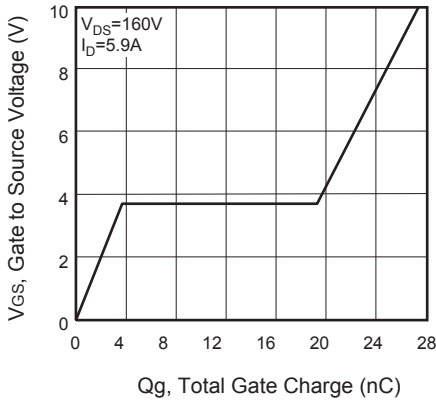


Figure 9. Switching Test Circuit

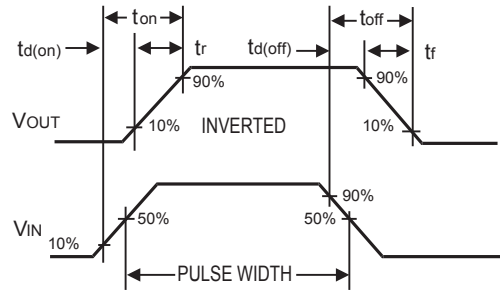


Figure 10. Switching Waveforms

